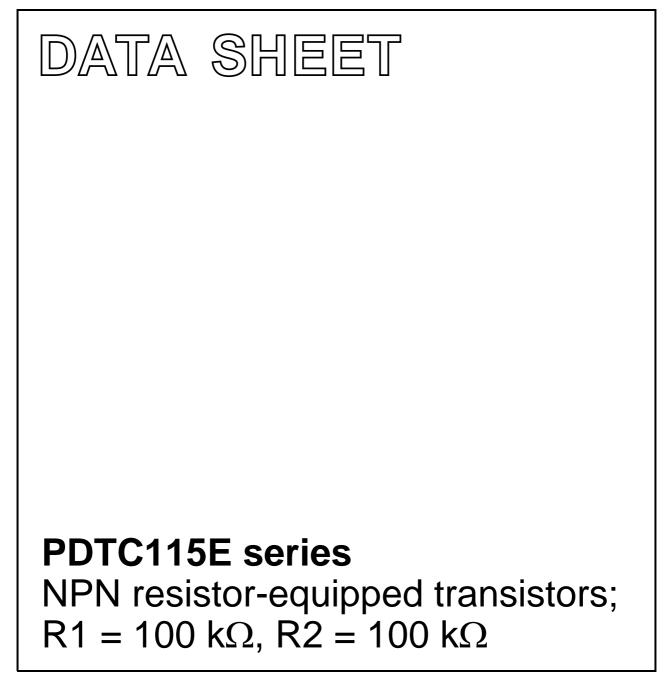
DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 2004 Apr 06 2004 Aug 06



PDTC115E series

FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

PRODUCT OVERVIEW

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT	
V _{CEO}	collector-emitter voltage	-	50	V	
lo	output current (DC)	-	20	mA	
R1	bias resistor	100	-	kΩ	
R2	bias resistor	100	-	kΩ	

DESCRIPTION

NPN resistor equipped transistor (see "Simplified outline, symbol and pinning" for package details).

TYPE NUMBER	PACKAGE				
	PHILIPS	EIAJ	MARKING CODE	PNP COMPLEMENT	
PDTC115EE	SOT416	SC-75	46	PDTA115EE	
PDTC115EEF	SOT490	SC-89	49	PDTA115EEF	
PDTC115EK	SOT346	SC-59	56	PDTA115EK	
PDTC115EM	SOT883	SC-101	DV	PDTA115EM	
PDTC115ES	SOT54 (TO-92)	SC-43	TC115E	PDTA115ES	
PDTC115ET	SOT23	_	*44 ⁽¹⁾	PDTA115ET	
PDTC115EU	SOT323	SC-70	*15 ⁽¹⁾	PDTA115EU	

Note

- 1. * = p: Made in Hong Kong.
 - * = t: Made in Malaysia.
 - * = W: Made in China.

PDTC115E series

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

			PINNING		
TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PIN	DESCRIPTION		
PDTC115ES		1 2 3	base collector emitter		
PDTC115EE		1	base		
PDTC115EEF		2	emitter		
PDTC115EK PDTC115ET PDTC115EU		3	collector		
	1 2 Top view MDB269				
PDTC115EM		1	base		
		2	emitter		
	2 1 bottom view MHC506	3	collector		

PDTC115E series

ORDERING INFORMATION

		PACKAGE			
TYPE NUMBER	NAME	DESCRIPTION			
PDTC115EE	-	plastic surface mounted package; 3 leads	SOT416		
PDTC115EEF	-	 plastic surface mounted package; 3 leads 			
PDTC115EK	-	 plastic surface mounted package; 3 leads 			
PDTC115EM	- leadless ultra small plastic package; 3 solder lands; body $1.0 \times 0.6 \times 0.5$ mm		SOT883		
PDTC115ES	 plastic single-ended leaded (through hole) package; 3 leads 		SOT54		
PDTC115ET	 plastic surface mounted package; 3 leads 		SOT23		
PDTC115EU	-	plastic surface mounted package; 3 leads			

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	-	50	V
V _{CEO}	collector-emitter voltage	open base	-	50	V
V _{EBO}	emitter-base voltage	open collector	_	10	V
VI	input voltage				
	positive		_	+40	V
	negative		_	-10	V
lo	output current (DC)		-	20	mA
I _{CM}	peak collector current		_	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT54	note 1	_	500	mW
	SOT23	note 1	_	250	mW
	SOT346	note 1	_	250	mW
	SOT323	note 1	_	200	mW
	SOT416	note 1	_	150	mW
	SOT883	notes 2 and 3	_	250	mW
	SOT490	notes 1 and 2	-	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μ m copper strip line.

PDTC115E series

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	in free air		
	SOT54	note 1	250	K/W
	SOT23	note 1	500	K/W
	SOT346	note 1	500	K/W
	SOT323	note 1	625	K/W
	SOT416	note 1	833	K/W
	SOT833	notes 2 and 3	500	K/W
	SOT490	notes 1 and 2	500	K/W

Notes

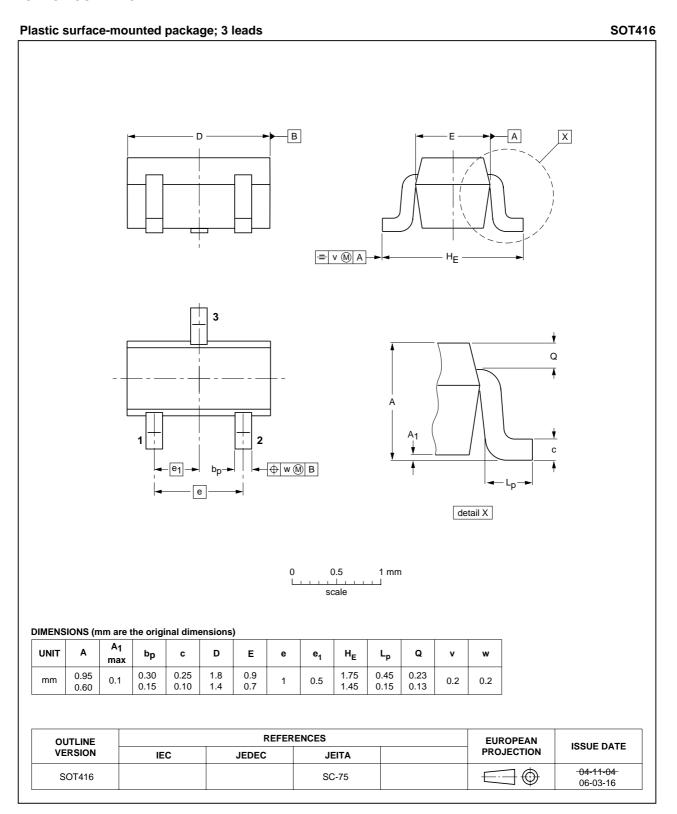
- 1. Refer to standard mounting conditions.
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- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μ m copper strip line.

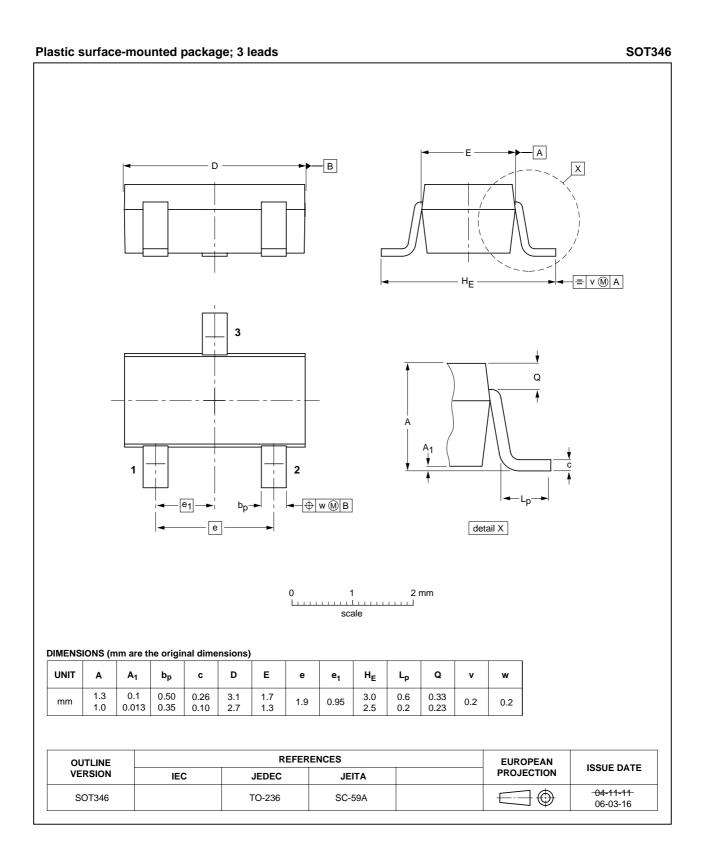
CHARACTERISTICS

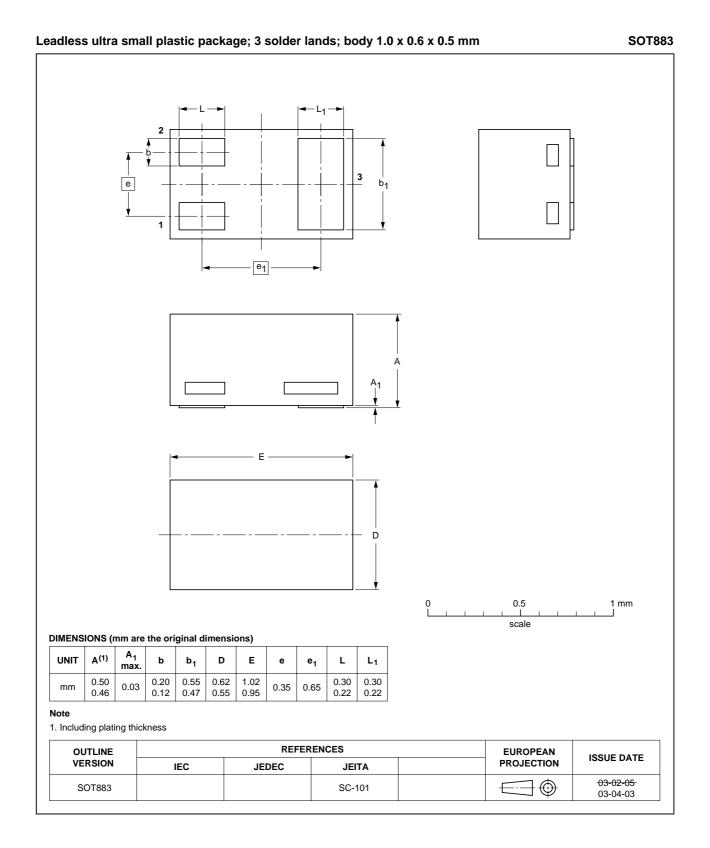
 T_{amb} = 25 °C unless otherwise specified.

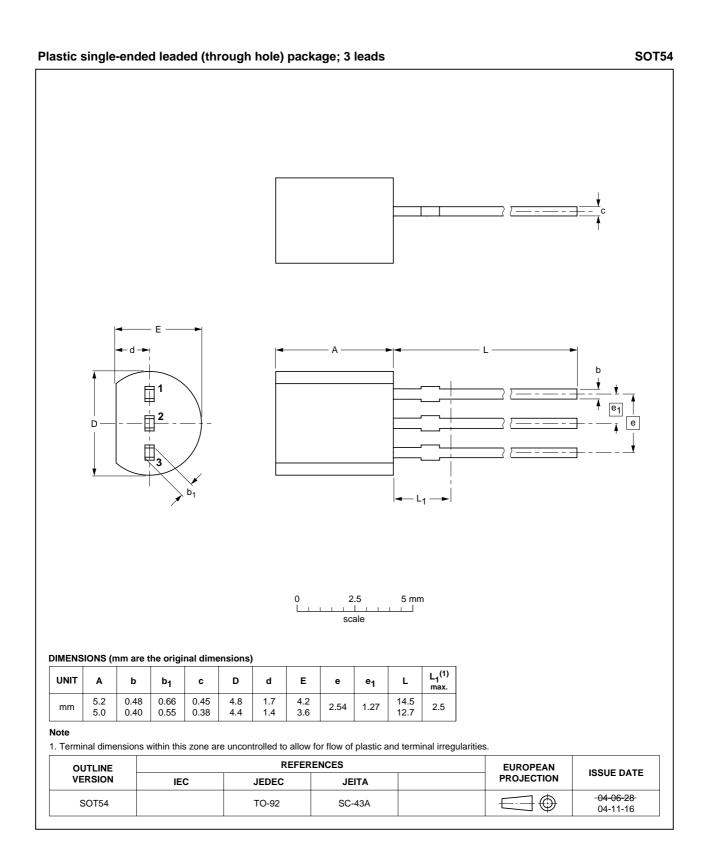
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; \text{ I}_{E} = 0 \text{ A}$	_	_	100	nA
I _{CEO}	collector-emitter cut-off current	V _{CE} = 30 V; I _B = 0 A	_	_	1	μA
		$V_{CE} = 30 \text{ V}; \text{ I}_{B} = 0 \text{ A}; \text{ T}_{j} = 150 ^{\circ}\text{C}$	_	_	50	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A	-	-	50	μA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$	80	-	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = 5 mA; I _B = 0.25 mA	_	_	150	mV
V _{i(off)}	input-off voltage	$I_{C} = 100 \ \mu A; V_{CE} = 5 \ V$	-	1.1	0.5	V
V _{i(on)}	input-on voltage	I _C = 1 mA; V _{CE} = 0.3 V	3	1.5	-	V
R1	input resistor		70	100	130	kΩ
<u>R2</u> R1	resistor ratio		0.8	1	1.2	
C _c	collector capacitance	$I_E = i_e = 0 \text{ A}; V_{CB} = 10 \text{ V};$ f = 1 MHz	-	_	2.5	pF

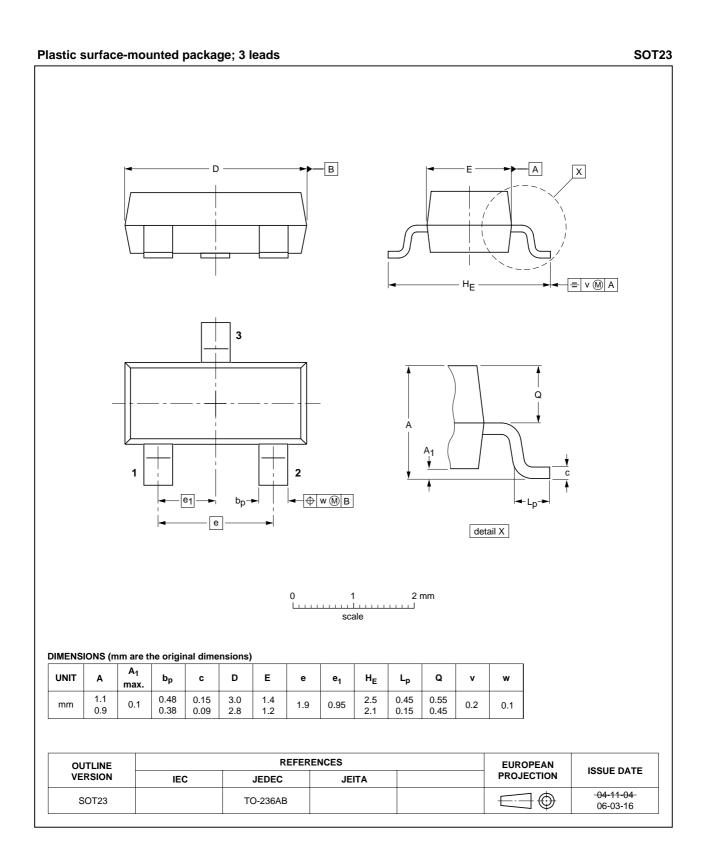
PACKAGE OUTLINES

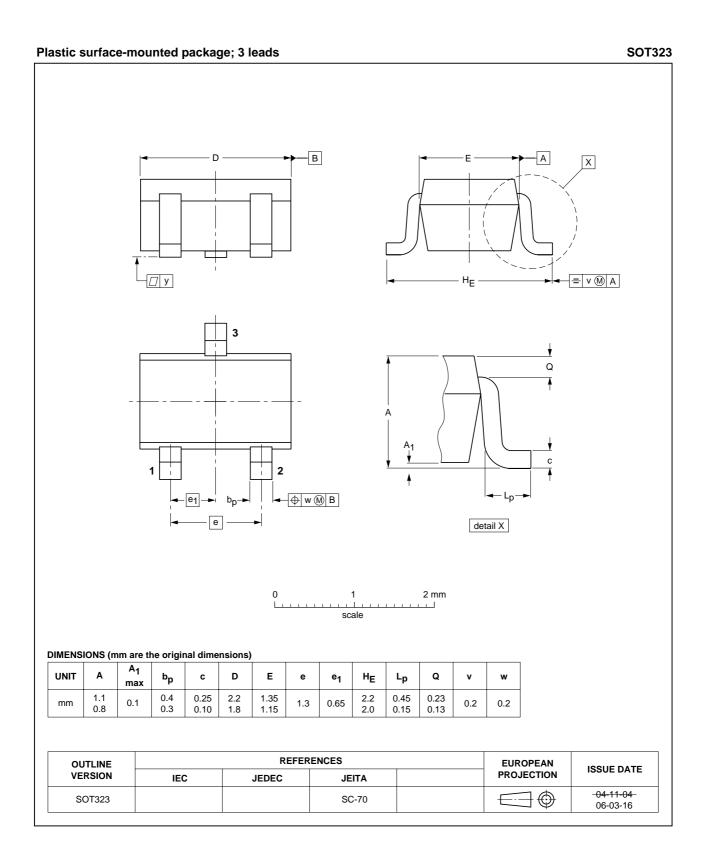


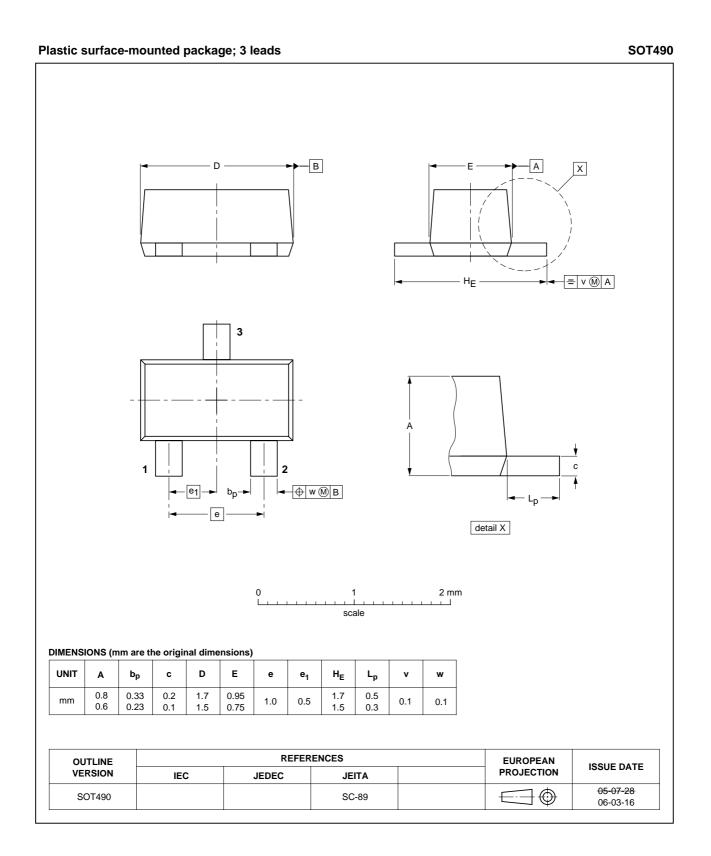












PDTC115E series

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com For sales offices addresses send e-mail to: salesaddresses@nxp.com

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